

CIR-V3DESI1304G

DDR3 DIMM 1333MHz 4GB with ECC

Description

The CIR-V3DESI1304G is 512M words X 72 bits, 2 ranks. Unbuffered Dual In-Line Memory Module (ECC-DIMM). DDR3 SDRAMs in Fine Ball Grid Array(FBGA) packages on a 240pin glass-epoxy substrate. Provide a high performance 8 byte interface in 133.35mm width form factor of industry standard. It is suitable for easy interchange and addition.

Specifications

Density	4GB
Pin Count	240pin
Type	Unbuffered
Dimensions	133.35mm x 30.0mm
ECC	With ECC
Component Config	256M x 8 bit
Data Rate	1333MHz
CAS Latency	9
Voltage	1.5V / 1.35V
PCB Layers	8
Operating Temp.(TCASE)	0°C~+85°C
Module Ranks	Dual Rank

Features

- JEDEC Standard 240-pin Dual In-Line Memory Module
- Power Supply: VDD= 1.5V (1.425V to 1.575V) & VDD= 1.35V (1.283V to 1.45V)
- Golden Connector (Au: 30u")
- Inputs and Outputs are SSTL-15 compatible
- CAS (READ) latency (CL): 6, 7, 8, 9
- Bi-Directional Differential Data Strobe
- DLL aligns DQ and DQS transition with CK transition
- Eight Internal banks for concurrent operation (components)
- Refresh: Auto-refresh, self-refresh
- Burst Length (BL) switch on-the-fly BL8 or BC4(Burst Chop)
- Support ECC function
- On-Die-Termination (ODT) for better signal quality
- RoHS Compliant (Lead Free) Memory module

